

PCN Number:	20140715000			PCN Date:	07/15/2014
Title:	Qualification of Fluorine Free ILD on CMOS9T 5V technology.				
Customer Contact:	PCN Manager	Phone:	+1(214)480-6037	Dept:	Quality Services
*Proposed 1st Ship Date:	10/15/2014	Estimated Sample Availability:	Date Provided at Sample request		
Change Type:					
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Assembly Materials
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials	<input checked="" type="checkbox"/>	Wafer Fab Process
		<input type="checkbox"/>	Part number change		
PCN Details					
Description of Change:					
This change notification is to announce the qualification of Fluorine Free ILD dielectric composition on the CMOS9T 5V technology.					
Current					
Chip Site	Fab Process	Wafer Diameter	Fluorine ILD Composition		
MAINEFAB	CMOS9T 5V	200mm	HDP = 4.5%, FSG=6.0%		
New					
Chip Site	Fab Process	Wafer Diameter	Fluorine ILD Composition		
MAINEFAB	CMOS9T 5V	200mm	0%		
Reason for Change:					
Continuity of supply.					
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):					
None					
Changes to product identification resulting from this PCN:					
None					
Product Affected:					
ADS1293CISQ/NOPB	LDC1000NHRR	LMP90507CISQX/NOPB	LMP91300NHZR		
ADS1293CISQE/NOPB	LDC1000NHRT	LMP91010DGSR	LMP91300NHZT		
ADS1293CISQX/NOPB	LMP90507CISQ/NOPB	LMP91010DGST	LMP91300YZRR		
LDC1000NHRJ	LMP90507CISQE/NOPB	LMP91300NHZJ	LMP91300YZRT		

Reference Qualification Data: CMOS9T-5V Fluorine Free Process

Qualification Data: (Approved 4/16/2013)

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qualification Device: LM3533TME (MSL LEVEL1-260C)

Package Construction Details

Wafer Fab Site:	MAINEFAB	Wafer Fab Process:	CMOS9T 5V
Wafer Diameter:	200mm	Metallization:	Al .5%Cu
Passivation:	OXIDE/NITRIDE		

Qualification: Plan Test Results

Reliability Test	Conditions	Sample Size / Fail	
		Lot# 1	Lot# 2
High Temp Operating Life	125C (1000 Hrs)	77/0	-
Temp Cycle	-65/150C (500 Cyc)	77/0	77/0

**Preconditioning: MSL1@260C

Qualification Data: (Approved 4/23/2013)

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qualification Device: LM8330TME/NOPB (MSL LEVEL1-260C)

Package Construction Details

Wafer Fab Site:	MAINEFAB	Wafer Fab Process:	CMOS9T 5V
Wafer Diameter:	200mm	Metallization:	Al .5%Cu
Passivation:	OXIDE/NITRIDE		

Qualification: Plan Test Results

Reliability Test	Conditions	Sample Size / Fail	
		Lot# 1	Lot# 2
High Temp Operating Life	150C (500 Hrs)	77/0	-

**Preconditioning: MSL1@260C

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com